

# Amplifier Transistors

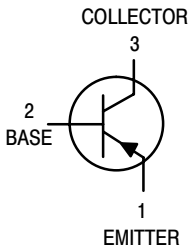
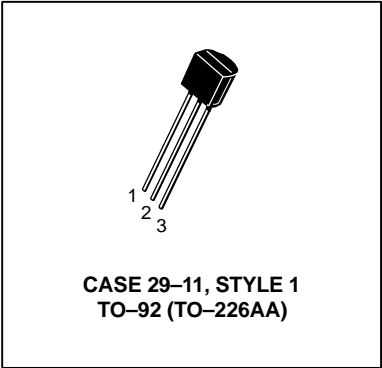
## PNP Silicon

# 2N5401\*

\*ON Semiconductor Preferred Device

### MAXIMUM RATINGS

Rating	Symbol	2N5400	2N5401	Unit
Collector–Emitter Voltage	$V_{CEO}$	120	150	Vdc
Collector–Base Voltage	$V_{CBO}$	130	160	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0		Vdc
Collector Current — Continuous	$I_C$	600		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625	5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5	12	Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150		°C



### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	2N5400 2N5401	$V_{(BR)CEO}$	150	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu\text{Adc}, I_E = 0$ )	2N5400 2N5401	$V_{(BR)CBO}$	160	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu\text{Adc}, I_C = 0$ )		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 120 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$ )	2N5401 2N5401	$I_{CBO}$	— —	50 50	
Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_C = 0$ )		$I_{EBO}$	—	50	nAdc

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

## 2N5401

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS(1)</b>				
DC Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$h_{FE}$	50 60 50	— 240 —	—
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	$V_{CE(sat)}$	— —	0.2 0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	$V_{BE(sat)}$	— —	1.0 1.0	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	$f_T$	100	300	MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{obo}$	—	6.0	pF
Small–Signal Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{fe}$	40	200	—
Noise Figure ( $I_C = 250 \mu\text{A}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $R_S = 1.0 \text{ k}\Omega$ , $f = 1.0 \text{ kHz}$ )	NF	—	8.0	dB

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2.0%.

# 2N5401

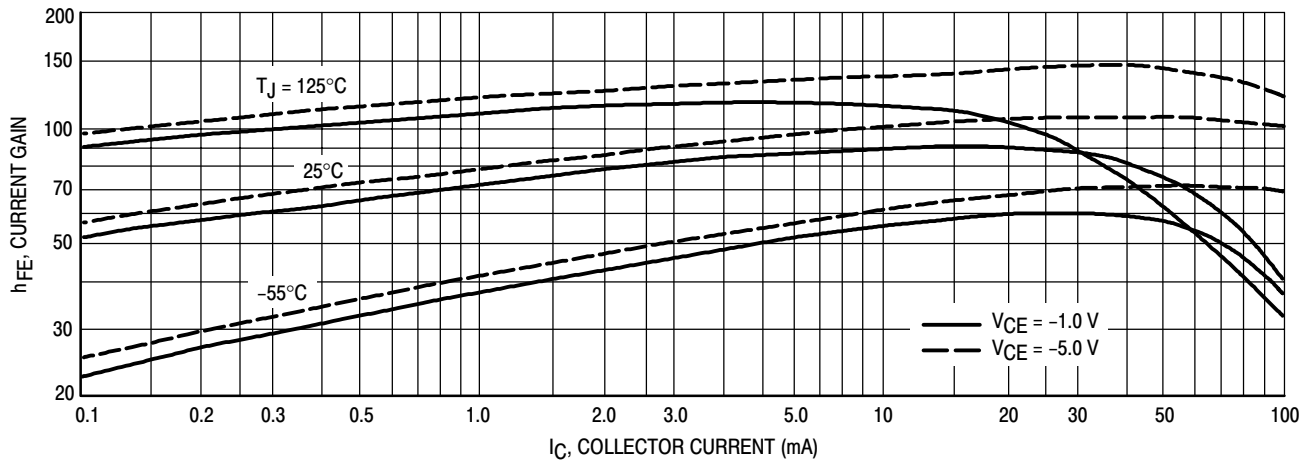


Figure 1. DC Current Gain

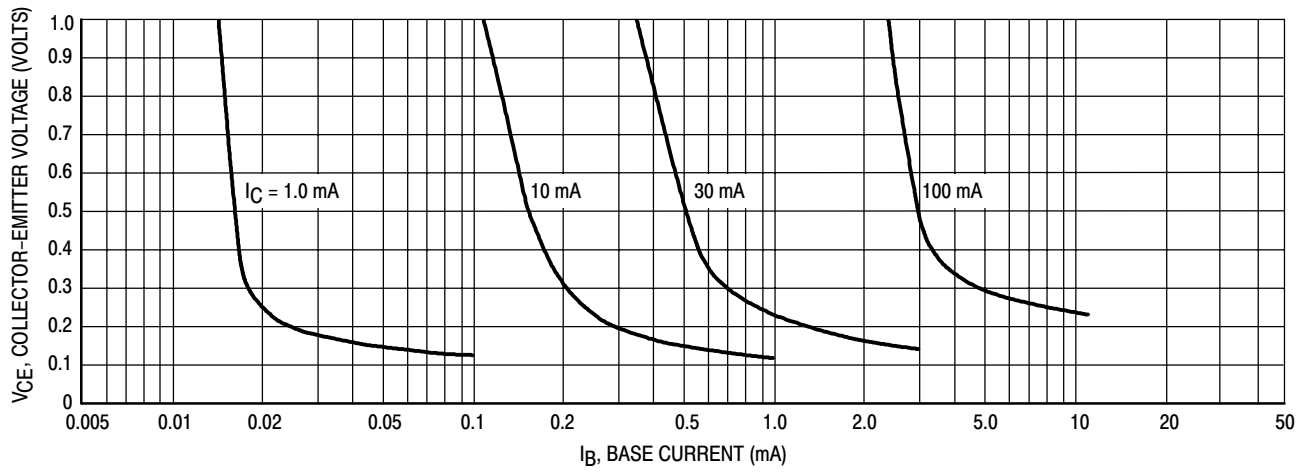


Figure 2. Collector Saturation Region

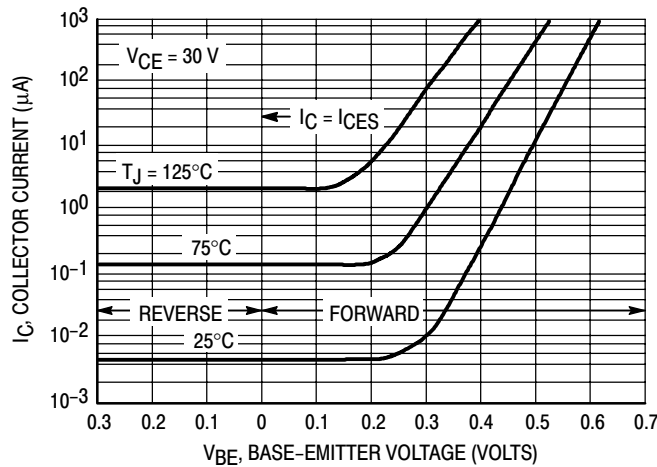


Figure 3. Collector Cut-Off Region

# 2N5401

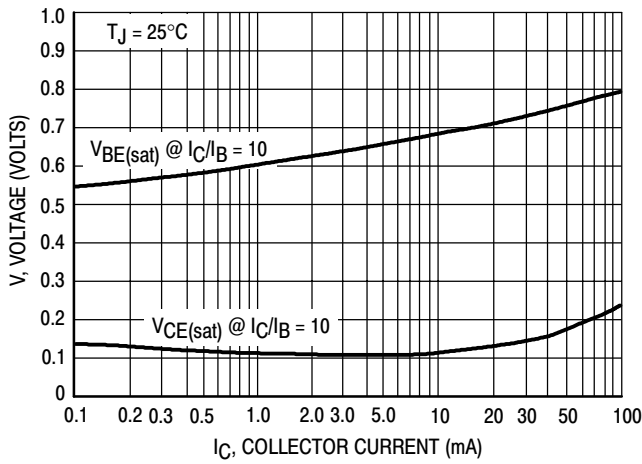


Figure 4. "On" Voltages

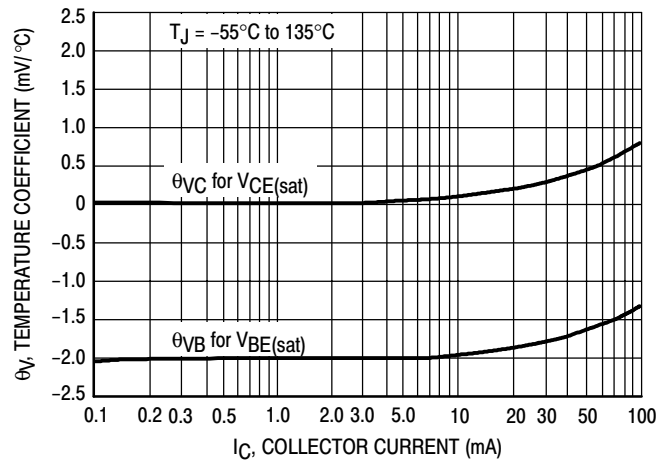


Figure 5. Temperature Coefficients

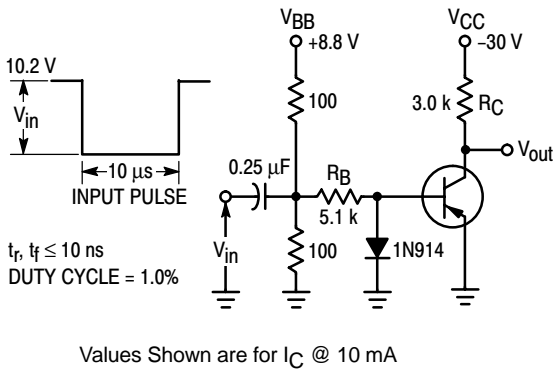


Figure 6. Switching Time Test Circuit

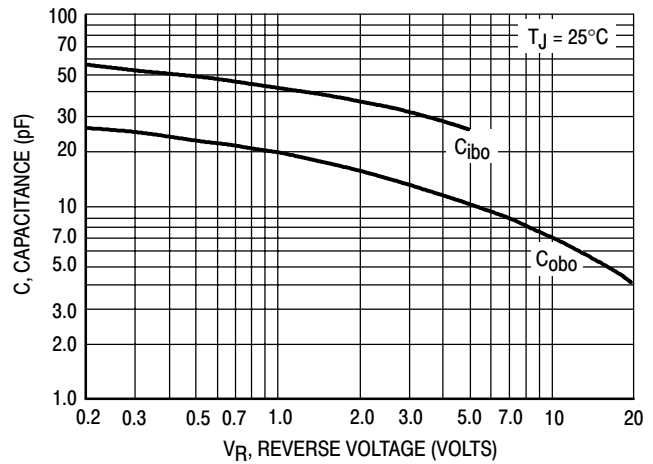


Figure 7. Capacitances

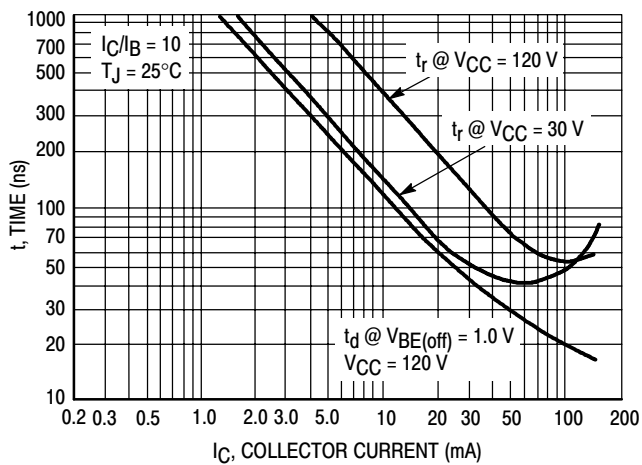


Figure 8. Turn-On Time

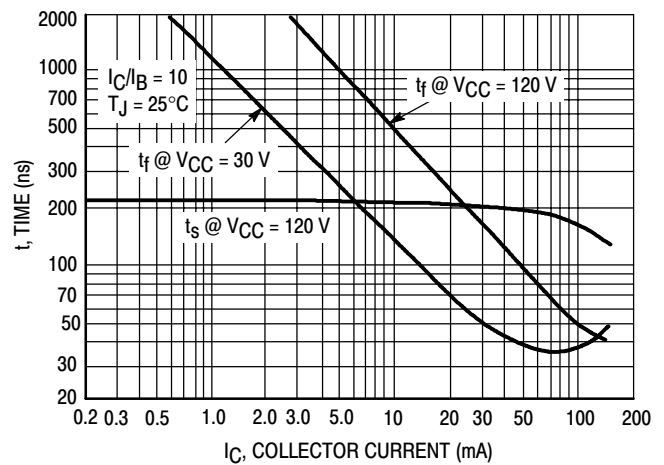
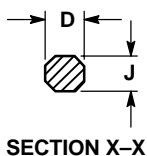
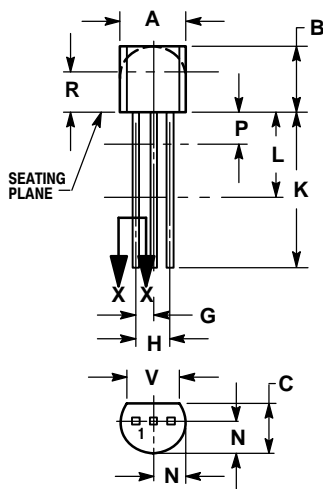


Figure 9. Turn-Off Time

# 2N5401

## PACKAGE DIMENSIONS

### TO-92 (TO-226) CASE 29-11 ISSUE AL



STYLE 1:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

**Notes**

**Notes**

**ON Semiconductor** and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

## PUBLICATION ORDERING INFORMATION

### Literature Fulfillment:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** ONlit@hibbertco.com

**N. American Technical Support:** 800-282-9855 Toll Free USA/Canada

**JAPAN:** ON Semiconductor, Japan Customer Focus Center  
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031  
**Phone:** 81-3-5740-2700  
**Email:** r14525@onsemi.com

**ON Semiconductor Website:** <http://onsemi.com>

For additional information, please contact your local Sales Representative.